

<b>SANYO</b>	No.679F	<b>2SB775/2SD895</b>
2SB775 : PNP Epitaxial Planar Silicon Transistor 2SD895 : NPN Triple Diffused Planar Silicon Transistor		
<b>85V/6A, AF 35W Output Applications</b>		

**Features**

- Wide ASO because of on-chip ballast resistance.
- Capable of being mounted easily because of one-point fixing type plastic molded package (Interchangeable with TO-3).
- Large current capacity ( $I_C = 6A$ ).
- Highly resistant to breakdown due to wide ASO.

( ) : 2SB775

**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

			unit
Collector-to-Base Voltage	$V_{CB0}$	(-) $100$	V
Collector-to-Emitter Voltage	$V_{CEO}$	(-) $85$	V
Emitter-to-Base Voltage	$V_{EBO}$	(-) $6$	V
Collector Current	$I_C$	(-) $6$	A
Collector Current (Pulse)	$I_{CP}$	(-) $10$	A
Collector Dissipation	$P_C$	$60$	W
Junction Temperature	$T_j$	$150$	$^\circ C$
Storage Temperature	$T_{stg}$	$-40$ to $+150$	$^\circ C$

$T_c = 25^\circ C$

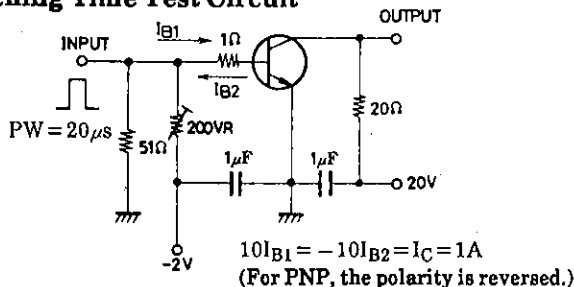
**Electrical Characteristics at  $T_a = 25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)40V, I_E = 0$			(-) $0.1$	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(-) $0.1$	mA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)5V, I_C = (-)1A$	$60^*$		$200^*$	
	$h_{FE}(2)$	$V_{CE} = (-)5V, I_C = (-)3A$	$20$			
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)5V, I_C = (-)1A$		( $18$ ) $15$		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = (-)10V, f = 1MHz$		$160$		pF
Base-to-Emitter Voltage	$V_{BE}$	$V_{CE} = (-)5V, I_C = (-)1A$			(-) $1.5$	V
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)4A, I_B = (-)0.4A$	(-) $1.4$	(-) $2.0$		V
			$0.9$	$2.0$		
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)5mA, I_E = 0$	(-) $100$			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)5mA, R_{BE} = \infty$	(-) $85$			V
		$I_C = (-)50mA, R_{BE} = \infty$	(-) $85$			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)5mA, I_C = 0$	(-) $6$			V
Turn-ON Time	$t_{on}$	See specified Test Circuit.	( $0.12$ ) $0.20$			$\mu s$
Fall Time	$t_f$	"	( $0.36$ ) $0.82$			$\mu s$
Storage Time	$t_{stg}$	"	( $1.29$ ) $3.88$			$\mu s$

\* : The 2SB775/2SD895 are classified by 1A  $h_{FE}$  as follows.

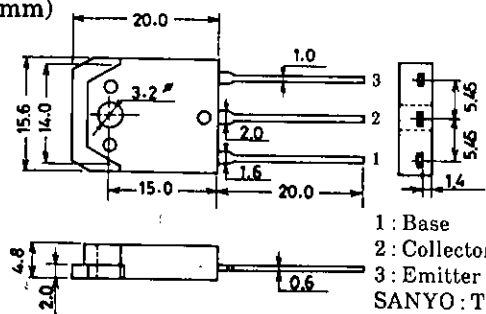
60	D	120	100	E	200
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**Switching Time Test Circuit**



**Package Dimensions 2022A**

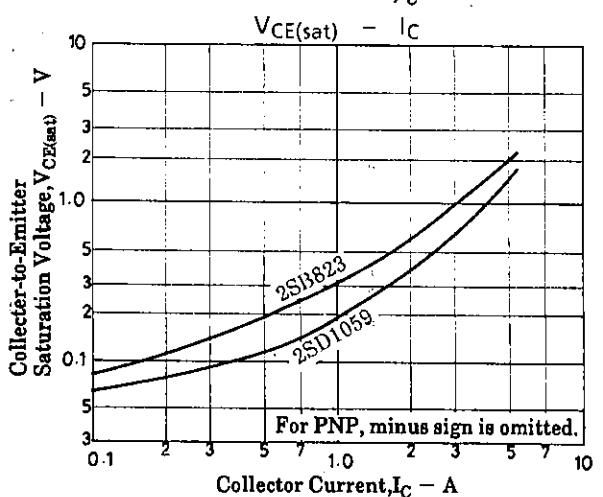
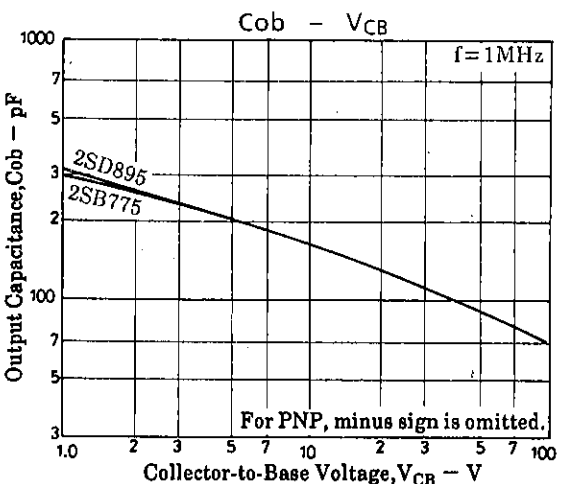
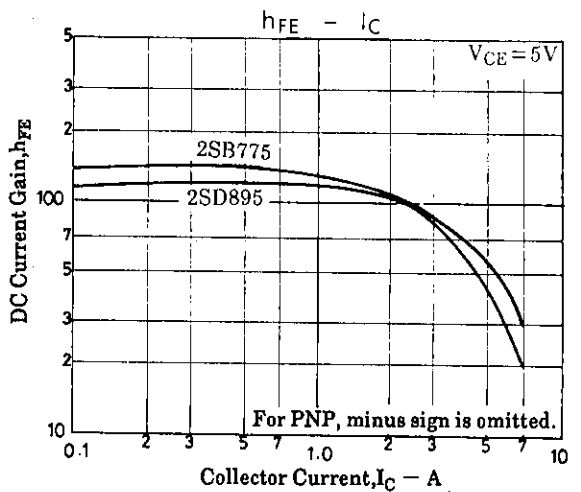
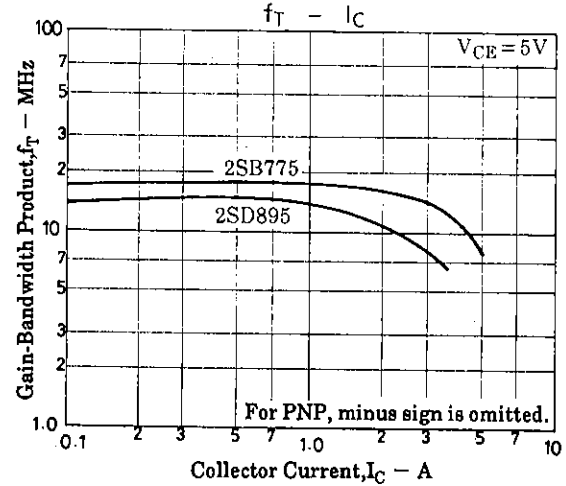
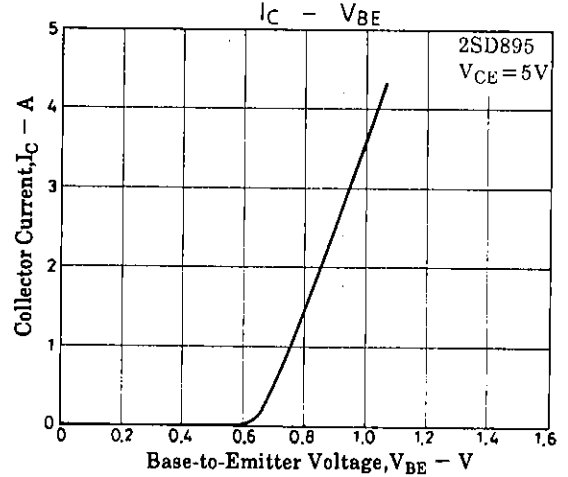
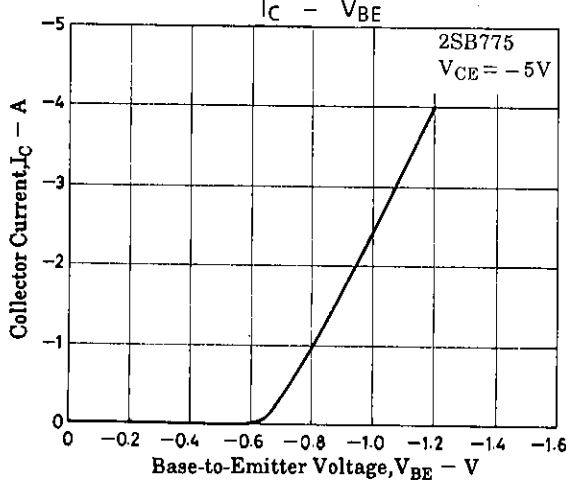
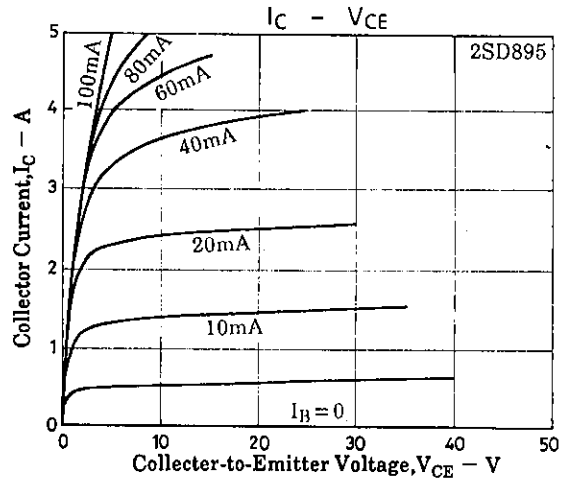
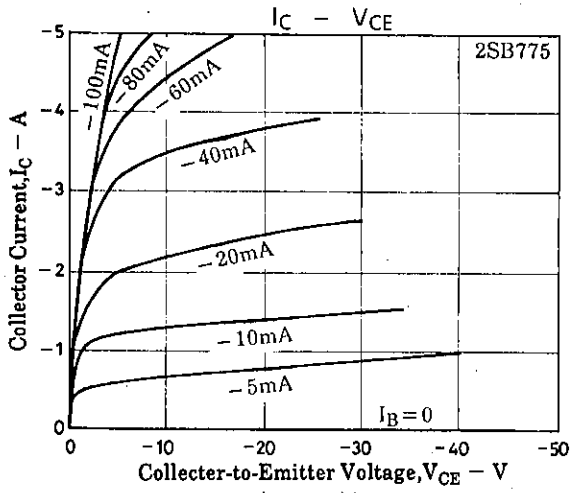
(unit : mm)



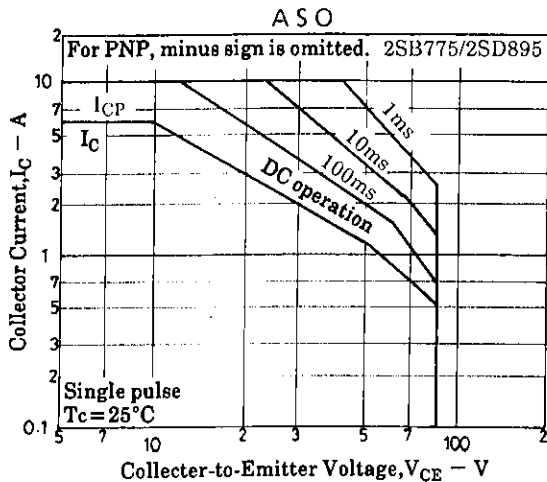
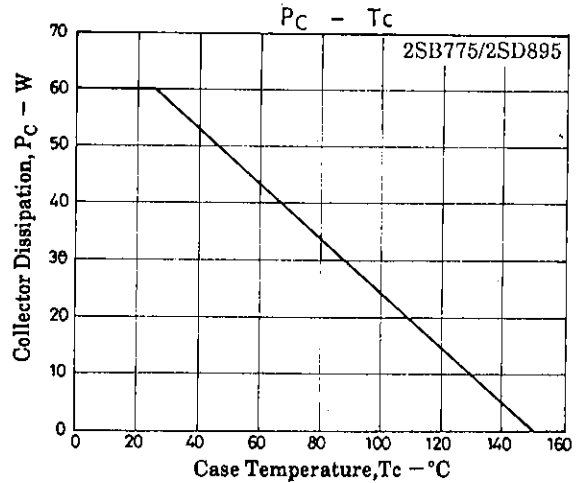
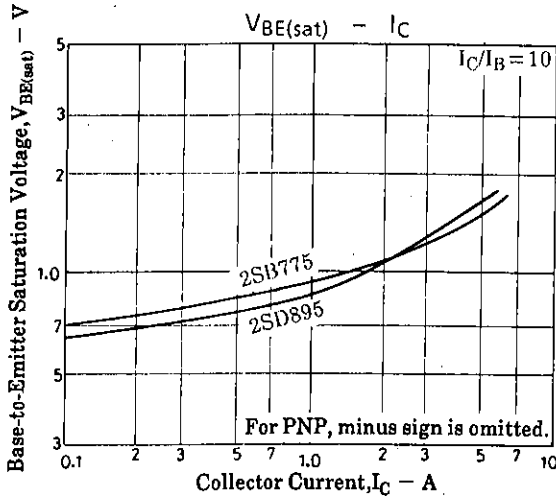
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2SB775/2SD895



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